

# 2MBI600VXA-120E-54

**IGBT Modules** 

# **IGBT MODULE (V series)** 1200V / 600A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



#### Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum ratings	Units	
Collector-Emitter voltage	Vces			1200	V	
Gate-Emitter voltage	V <sub>GES</sub>			±20	V	
	Ic	Continuous	Tc=25°C	800		
Ţ			Tc=100°C	600		
© Collector current	I <sub>c pulse</sub>	1ms		1200	Α	
=	-Ic	1ms		600		
	-I <sub>c pulse</sub>			1200		
Collector power dissipation	Pc	1 device		3350	W	
Junction temperature	Tj			175		
Operating junction temperature (under switching conditions)	Tjop			150	°C	
Case temperature	Tc			150		
Storage temperature	T <sub>stg</sub>			-40 ~ +150		
Isolation voltage between terminal and copper base (*1)	V <sub>iso</sub>	AC : 1min.		4000	VAC	
between thermistor and others (*2)	Viso			4000	VAC	
Mounting		M5		6.0	N m	
Screw torque (*3) Main Terminals	]-	M8		10.0		
Sense Terminals		M4		2.1		

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable Value: Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value: Main Terminals 8.0 ~ 10.0 Nm (M8)

Recommendable Value: Sense Terminals 1.8 ~ 2.1 Nm (M4)

# ● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Cumbala	Symbols Conditions		Characteristics			Units	
		Symbols			min.	typ.	max.	Units	
Inverter	Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V		-	-	4.0	mA	
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$		-	-	800	nA	
	Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 600mA		6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V <sub>CE (sat)</sub>		T <sub>j</sub> =25°C	-	1.85	2.30	V	
		(terminal)		T <sub>j</sub> =125°C	-	2.15	-		
		(*4)	V <sub>GE</sub> = 15V I <sub>C</sub> = 600A	T <sub>j</sub> =150°C	-	2.20	-		
		.,		T <sub>j</sub> =25°C	-	1.75	2.20		
		V <sub>CE</sub> (sat)		T <sub>j</sub> =125°C	-	2.05	-		
		(chip)		T <sub>j</sub> =150°C	-	2.10	-		
	Internal gate resistance	Rg <sub>(int)</sub>	-		-	1.75	-	Ω	
		Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	55	-	nF	
	Turn-on time	ton	V <sub>cc</sub> = 600V	-	1000	-	nsec		
		t	Ic = 600A	-	400	-			
		t <sub>r (i)</sub>	V <sub>GE</sub> = ±15V	-	150	-			
	Turn-off time	toff	$R_G = 2.4\Omega$		-	1200	-	1	
		t <sub>f</sub>	Ls = 70nH	_	150	-	1		
	Forward on voltage	VF		T <sub>i</sub> =25°C	-	1.80	2.25		
		(terminal)		T <sub>i</sub> =125°C	-	1.95	-		
		(*4)	V <sub>GE</sub> = 0V	T <sub>i</sub> =150°C	-	1.90	-	١,,	
		,,	I <sub>F</sub> = 600A	T <sub>i</sub> =25°C	-	1.70	2.15	V	
		VF		T <sub>i</sub> =125°C	-	1.85	-	1	
		(chip)		T <sub>i</sub> =150°C	-	1.80	-		
	Reverse recovery time	trr	I <sub>F</sub> = 600A		-	200	-	nsec	
ģ	Resistance		T=25°C		-	5000	-	Ω	
Thermistor		R	T=100°C		465	495	520		
The	B value	В	T=25/50°C	,	3305	3375	3450	К	

Note \*4: Please refer to page 6 , there is definition of on-state voltage at terminal.

#### ● Thermal resistance characteristics

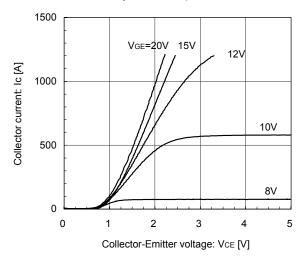
Itomo	Symbols	Conditions	Characteristics			Units
Items			min.	typ.	max.	Units
Thermal registeres (1 device)	Rth(j-c)	Inverter IGBT	-	-	0.045	°C/W
Thermal resistance (1device)		Inverter FWD	-	-	0.075	
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0125	-	

Note  $^{*}5$ : This is the value which is defined mounting on the additional cooling fin with thermal compound.

#### **■** Characteristics (Representative)

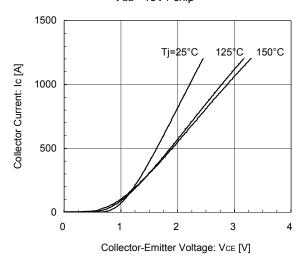
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



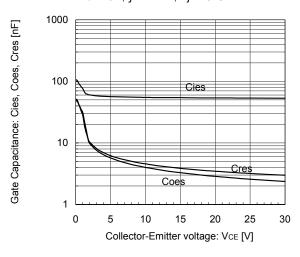
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



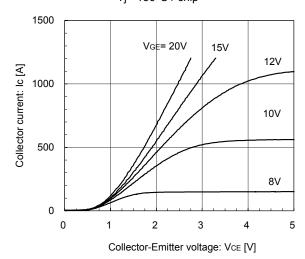
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.)  $V_{GE} = 0V, f = 1MHz, Tj = 25^{\circ}C$ 



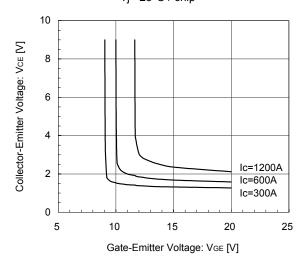
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Ti= 150°C / chip



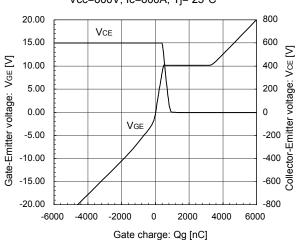
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip



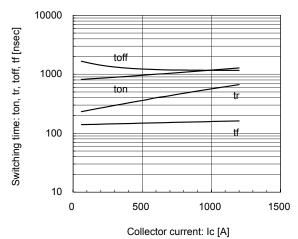
[INVERTER]

Dynamic Gate Charge (typ.) Vcc=600V, Ic=600A, Tj= 25°C



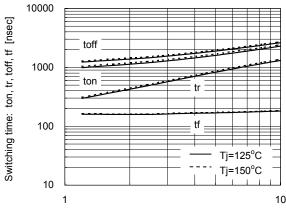
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg= $2.4\Omega$ , Tj= $25^{\circ}$ C



### [INVERTER]

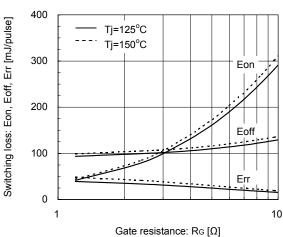
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VgE=±15V, Tj=125°C, 150°C



Gate resistance: R<sub>G</sub> [Ω]

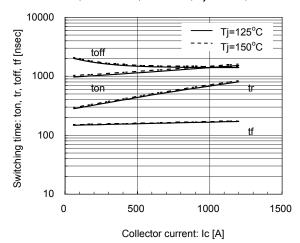
### [INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VgE= $\pm$ 15V, Tj=125°C, 150°C



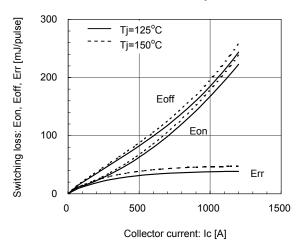
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg= $2.4\Omega$ , Tj= $125^{\circ}$ C,  $150^{\circ}$ C



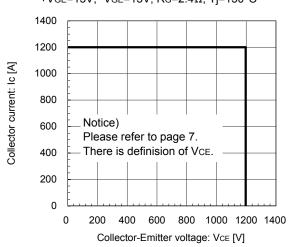
#### [INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V , VgE= $\pm$ 15V, Rg=2.4 $\Omega$ , Tj=125°C, 150°C

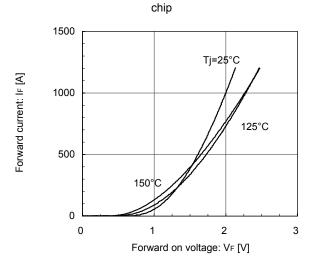


#### [INVERTER]

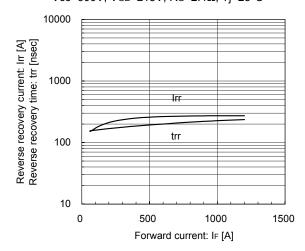
Reverse bias safe operating area (max.) +VgE=15V, -VgE=15V, Rg=2.4 $\Omega$ , Tj=150°C



[INVERTER] Forward Current vs. Forward Voltage (typ.)

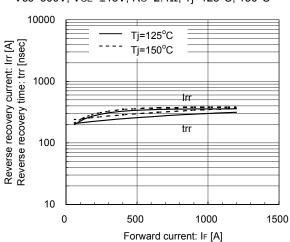


[INVERTER]
Reverse Recovery Characteristics (typ.)
Vcc=600V, VgE=±15V, Rg=2.4Ω, Tj=25°C

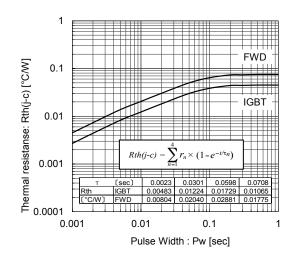


[INVERTER]

Reverse Recovery Characteristics (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg= $2.4\Omega$ , Tj= $125^{\circ}$ C,  $150^{\circ}$ C

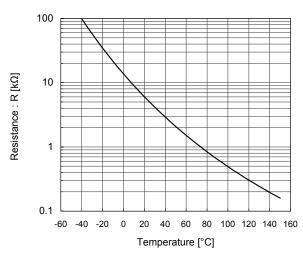


Transient Thermal Resistance (max.)

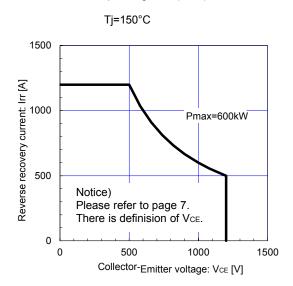


[THERMISTOR]

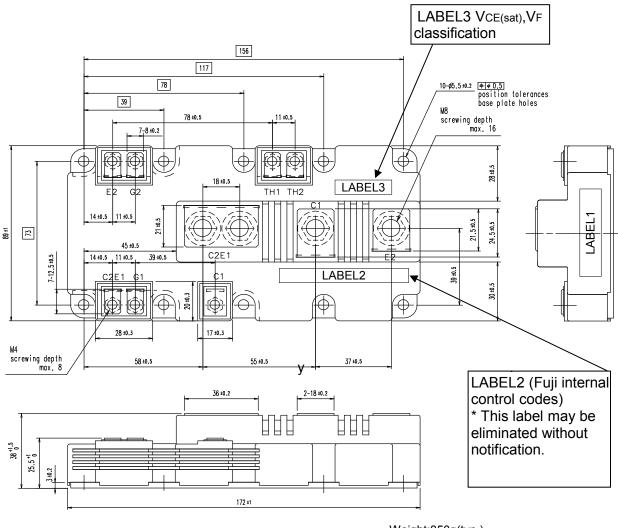
Temperature characteristic (typ.)



FWD safe operating area (max.)

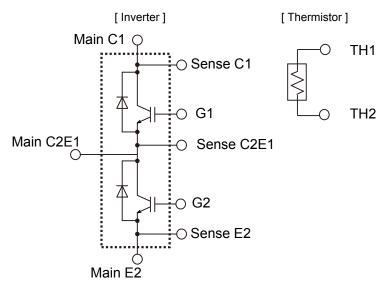


### ■ Outline Drawings, mm



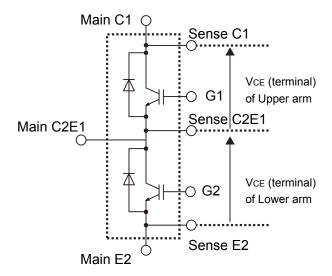
Weight:850g(typ.)

#### **■** Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

## ■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined VcE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

Switching characteristics of VcE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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